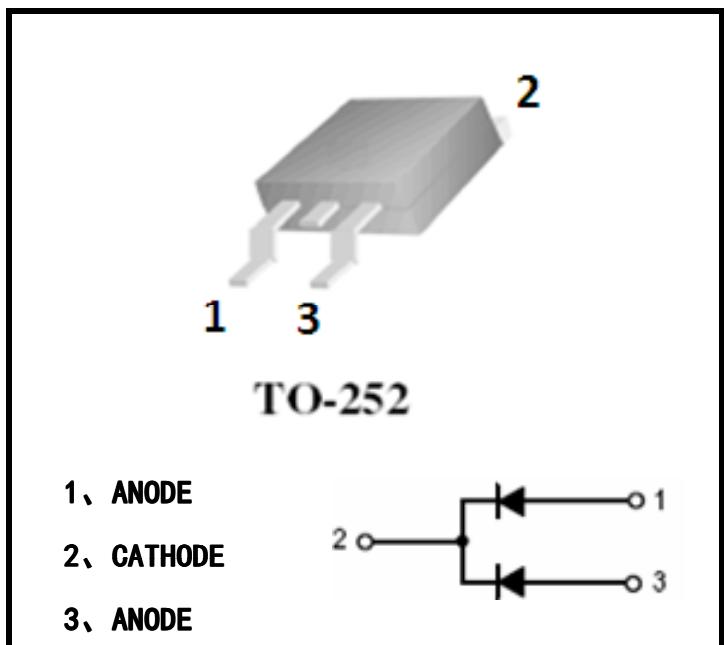


■ FEATURES

- * Schottky Barrier Chip
- * Guard Ring Die Construction for Transient Protection
- * Low Power Loss, High Efficiency
- * High Surge Capability
- * High Current Capability and Low Forward Voltage Drop
- * For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

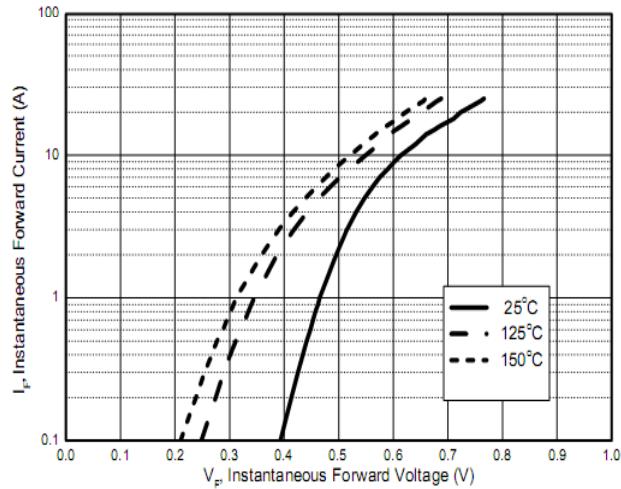
■ PACKAGE



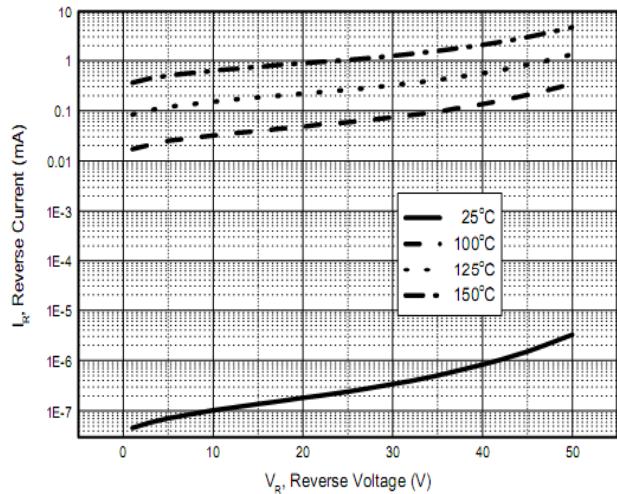
■ ELECTRICAL CHARACTERISTICS (T_{amb}=25°C)

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	45	V
Working Peak Reverse Voltage	V _{RWM}		
DC Blocking Voltage	V _R		
Average Rectified Output Current	I _{F(per leg)}	10	A
	I _{F(Total)}	20	
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60Hz)	I _{FSM}	200	A
Maximum Instantaneous Forward Voltage @ IF=10A, TC=25°C	V _F	0.65	V
Peak Reverse Current @ Tc=25 °C at Rated DC Blocking Voltage @ Tc=125°C	I _R	0.025 5	mA
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C
Maximum Thermal Resistance	θ _{JC}	3	°C/W
	θ _{JA}	60	

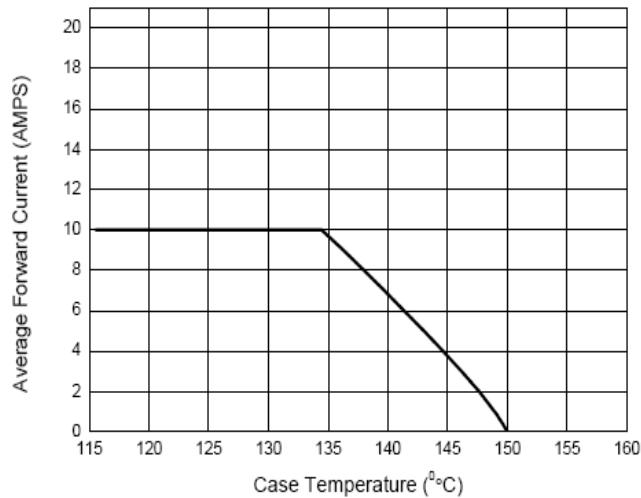
■ Characteristics Curves



Typical Forward Voltage

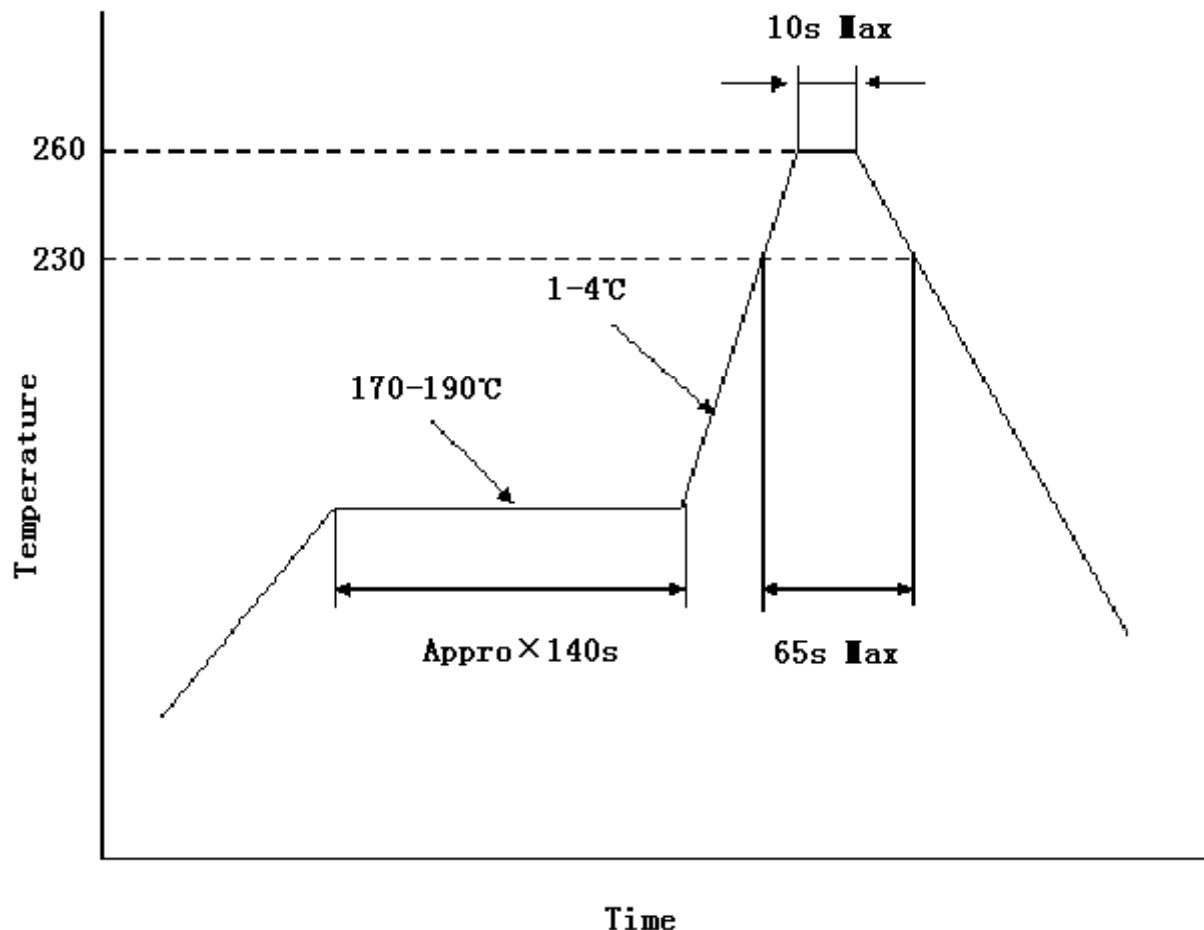


Typical Reverse Current



Average Forward Forward Current vs.
Case Temperature Per Diode

■ Reflow Soldering Temperature Profile



TO-252 MECHANICAL DATA

UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	2.10		2.50	E	5.80		6.30
B	0.80		1.25	e1	2.25	2.30	2.35
b	0.50		0.85	e2	4.45		4.75
b1	0.50		0.90	L1	9.50		10.20
b2	0.45		0.60	L2	0.90		1.45
C	0.45		0.60	L3	0.60		1.10
D	6.35		6.75	K	-0.1		0.10
D1	5.10		5.50				

